

Title (en)
PROCESS FOR PRODUCING A SILICON CAPACITOR

Title (de)
VERFAHREN ZUR HERSTELLUNG EINES SILIZIUMKONDENSATORS

Title (fr)
PROCEDE DE FABRICATION D'UN CONDENSATEUR AU SILICIUM

Publication
EP 0775370 A1 19970528 (DE)

Application
EP 95927642 A 19950807

Priority
• DE 9501036 W 19950807
• DE 4428195 A 19940809

Abstract (en)
[origin: DE4428195C1] In order to produce a silicon capacitor, holes are created in an n-doped silicon substrate (1); across the surface of the holes a conducting region (40) is created through doping and a dielectric layer (6) and a conducting layer (7) are provided. To compensate for mechanical stresses in the silicon substrate resulting from the doping of the conducting region (40), the conducting region (40) is in addition doped with germanium which diffuses out from a germanium-doped layer.

IPC 1-7
H01L 29/94; **H01L 21/334**

IPC 8 full level
H01L 27/04 (2006.01); **H01L 21/02** (2006.01); **H01L 21/822** (2006.01)

CPC (source: EP KR US)
H01L 21/76 (2013.01 - KR); **H01L 28/82** (2013.01 - EP US)

Citation (search report)
See references of WO 9605620A1

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